

Title (en)

SYSTEM AND METHOD FOR RECORDING THE CHARACTERISTIC CURVES OF LIGHT-EMITTING DIODES

Title (de)

SYSTEM UND VERFAHREN ZUR ERFASSUNG DER KENNLINIEN VON LEUCHTDIODEN (LEDS)

Title (fr)

SYSTÈME ET PROCÉDÉ D'ENREGISTREMENT DES CARACTÉRISTIQUES DE DIODES ÉLECTROLUMINESCENTES (LED)

Publication

EP 2160928 A2 20100310 (DE)

Application

EP 08773553 A 20080620

Priority

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Abstract (en)

[origin: WO2009000475A2] The invention relates to a system for recording characteristic curves for a light-emitting diode arrangement (1) comprising at least one light-emitting diode (2). A control unit (4) is used to operate the light-emitting diode arrangement (1) and to record the diode current (8) and the voltage (9) on the light-emitting diode arrangement (1). The control unit (4) is also used to record a first current/voltage pair (P1) and a different second current/voltage pair (P2), at a first temperature of the light-emitting diode arrangement (1), and a third current/voltage pair (P3) and a different fourth current/voltage pair (P4), at a second temperature of the light-emitting diode arrangement (1). The invention also relates to a method for recording characteristic curves of a light-emitting diode arrangement.

IPC 8 full level

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CPC (source: AT EP US)

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Citation (search report)

See references of WO 2009000475A2

Citation (examination)

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